



**HAL**  
open science

# Single-frequency optically pumped semiconductor vertical external cavity laser at 852nm for Cs atomic clock

Fabiola A. Camargo, Isabelle Sagnes, Arnaud Garnache, Patrick Georges, Gaëlle Lucas-Leclin

► **To cite this version:**

Fabiola A. Camargo, Isabelle Sagnes, Arnaud Garnache, Patrick Georges, Gaëlle Lucas-Leclin. Single-frequency optically pumped semiconductor vertical external cavity laser at 852nm for Cs atomic clock. CLEO Europe, May 2011, Munich, Germany. hal-00579994

**HAL Id: hal-00579994**

**<https://iogs.hal.science/hal-00579994v1>**

Submitted on 25 Mar 2011

**HAL** is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

## Single-frequency optically pumped semiconductor vertical external cavity laser at 852nm for Cs atomic clock

Fabiola A. Camargo<sup>1</sup>, Isabelle Sagnes<sup>2</sup>, Arnaud Garnache<sup>3</sup>, Patrick Georges<sup>1</sup> and Gaëlle Lucas-Leclin<sup>1</sup>

<sup>1</sup>Laboratoire Charles Fabry de l'Institut d'Optique, CNRS, Univ Paris-Sud, Campus Polytechnique RD 128, 91127 Palaiseau Cedex, France

<sup>2</sup>Laboratoire de Photonique et de Nanostructures, CNRS UPR20, Route de Nozay, 91460 Marcoussis, France

<sup>3</sup>Centre d'Electronique et de Micro-optoélectronique de Montpellier, CNRS UMR5507, Université Montpellier 2, 34095 Montpellier Cedex 5, France

\*Corresponding author e-mail : [fabiola.camargo@institutoptique.fr](mailto:fabiola.camargo@institutoptique.fr)

Stable single-frequency laser with narrow linewidth emission ( $< 500\text{kHz}$ ), fine tunability over a few GHz and output power in the  $0.1\text{W}$  range is required to cold atom interferometry experiments. Until now different approaches have been studied in order to fulfil all these characteristics. Single frequency high power lasers have been demonstrated with distributed feedback diode lasers and tapered extended cavity diode lasers. However, these two solutions suffer from beam quality degradation at high power. A possible alternative solution to obtain a compact and simple single frequency source with narrow linewidth and good beam quality is an optically-pumped semiconductor vertical external-cavity surface-emitting laser (OPS-VECSEL), which has already demonstrated multi watt output power in the fundamental transverse mode [1] as well as high power single frequency operation [2]. Nevertheless the majority of these works using VECSEL are focused around  $1\mu\text{m}$  emission. In this work we evaluate short external-cavities VECSEL for single-frequency emission at  $852\text{nm}$  dedicated to Cs atom spectroscopy.

The  $1/2$ -VCSEL chip has been grown by metal-organic chemical-vapor deposition on a  $350\mu\text{m}$  thick GaAs substrate. It is composed by a multilayer Distributed Bragg Reflector, consisted of 32.5 pairs of  $\text{AlAs}/\text{Al}_{0.225}\text{Ga}_{0.775}\text{As}$  quarter-wave layers resulting in a 99.95% reflectivity at  $852\text{nm}$ , and seven  $8\text{nm}$  thick GaAs quantum wells embedded between  $\text{Al}_{0.22}\text{Ga}_{0.78}\text{As}$  barriers. This chip is fixed on a copper heatsink, cooled by a Peltier element and optically pumped with a  $690\text{nm}$  fiber-coupled diode laser; the pump spot diameter is  $62\mu\text{m}$  on the structure. The  $2\text{mm}$  long cavity with a free spectral range of  $\sim 75\text{GHz}$  consists of the semiconductor and an output coupler mirror (Figure 1). Two configurations were studied: the first one uses a  $25\text{mm}$  curve mirror as the output coupler; in the second one a plane output coupler is used and the cavity is stabilized by the strong thermal lens generated in the semiconductor chip.

The maximum output power is  $106\text{mW}$  with the 2.1%-transmission concave mirror at a chip temperature of  $T = 15^\circ\text{C}$  (Figure 2). Both configurations are limited by the thermal roll-over around  $0.6\text{W}$  of incident power. However the plane-plane configuration has a three times higher laser threshold. Thanks to the short length of the cavity where only few longitudinal modes could oscillate, single frequency operation is obtained without any spectrally-selective intracavity element with a side-mode suppression ratio about  $35\text{dB}$ . Stable single-frequency emission within a wide operating range is demonstrated only for output coupler transmissions higher than 2% as high cavity losses reduce competition between adjacent longitudinal modes [3]. The laser line is tuned to the cesium optical transition ( $\sim 852.1\text{nm}$ ) by adjusting the semiconductor temperature and the cavity length.

These first promising results show the prospect of using compact VECSEL as a single frequency source for Cs atomic clocks. The detailed characterization of the spectral properties of the short VECSEL is under progress.

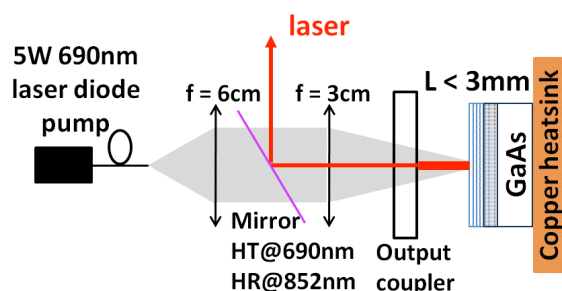


Fig. 1: Optically pumped VECSEL setup.

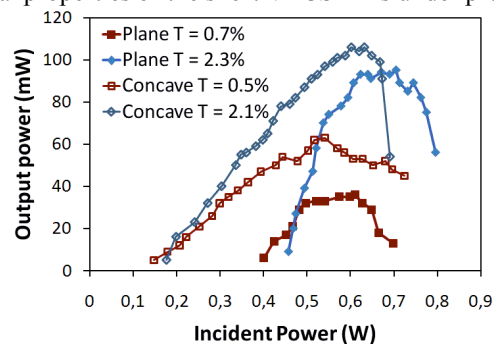


Fig. 2: Laser output power versus incident power for the different configuration and transmission output couplers used ( $T_{\text{substrate}} = 15^\circ\text{C}$ ).

### References

- [1] J. Chilla et al. "High Power Optically Pumped Semiconductor Lasers", Proc. of SPIE **5332**, 143 (2004).
- [2] A. Laurain et al. "Multiwatt-power highly-coherent compact single-frequency tunable Vertical-External-Cavity-Surface-Emitting-Semiconductor-Laser", Opt.Exp. **18** 14627 (2010).
- [3] A. Garnache et al. "Single-Frequency operation of External-Cavity VCSELs: Non-linear multimode temporal dynamics and quantum limit", Opt. Exp. **15**, 9403(2007).

**Acknowledgments :** The authors acknowledge the financial support of the Agence Nationale de la Recherche under the ANR-07-BLAN-0320-03 program.